TOSHIBA TLRH190P

TOSHIBA LED LAMP InGaA&P RED LIGHT EMISSION

TLRH190P

PANEL CIRCUIT INDICATOR

- 10mm DIAMETER
- InGaAlP RED LED
- All Plastic Mold Type.
- Colorless Clear Lens
- Low Drive Current, High Intensity Red Light Emission Recommended Forward Current: IF=1~20mA (DC)
- All Plastic Molded Lens, Provides an Excellent ON-OFF Contrast
- Fast Response Time, Capable of Pulse Operation.
- High Power Luminous Intensity
- Without Stand-offs
- APPLICATIONS: Suitable for Outdoor Message Signboard, Safety equipment.

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Forward Current (DC)	$I_{\mathbf{F}}$	50	mA
Reverse Voltage	$V_{\mathbf{R}}$	4	V
Power Dissipation	P_{D}	125	mW
Operating Temperature Range	$T_{ m opr}$	-30~85	°C
Storage Temperature Range	$T_{ m stg}$	-40~120	$^{\circ}\mathrm{C}$

Unit in mm ଉ CATHODE INDEX 1. ANODE 2. CATHODE **JEDEC EIAJ**

Weight: 1.0g

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ELECTRO-OPTICAL CHARACTERISTICS (Ta = 25°C)

CHAR	ACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Vo	ltage	$ m V_{f F}$	$I_{\mathbf{F}} = 20 \text{mA}$	_	1.9	2.5	V
Reverse Cur	rrent	$I_{\mathbf{R}}$	$V_R = 4V$	_	_	50	μ A
Luminous	TLRH190P	I_{V}	I _F =20mA (Note)	4760	15000	_	mcd
Intensity	TLRH190P (VW)			4760	_	23000	
Peak Emiss	ion Wavelength	$\lambda_{\mathbf{p}}$	$I_{ m F} = 20 { m mA}$	_	644	_	nm
Spectral Lir	ne Half Width	Δλ	$I_F = 20 mA$		18		nm
Dominant V	Vavelength	$^{\lambda}\mathbf{d}$	$I_{ m F}$ = 20mA	_	630	_	nm

(Note) Rank selection carried out under next range respectively, although it needs ±15% additionary for guaranteed limits.

V: 5600-11200, W: 10000-20000mcd, X: 18000-36000mcd.

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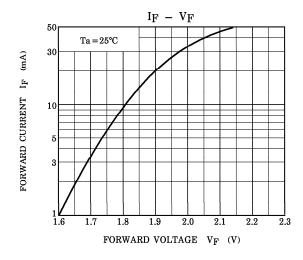
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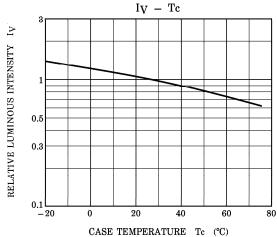
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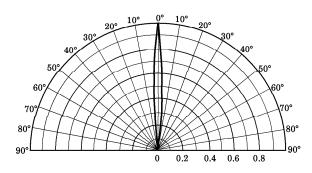
PRECAUTION

Please be careful of the followings

- Soldering temperature: 260°C MAX. Soldering time: 3s MAX. (Soldering portion of lead: up to 2mm from the body of the device)
- If the lead is formed, the lead should be formed up to 5mm from the body of the device without forming stress to the resin. Soldering should be performed after lead forming.







RADIATION PATTERN

Ta = 25°C

